

5TH SEM. / ETC & COMM. / ETC. & TELECOM. / 2022(W)

Th-2 VLSI & Embedded System

Full Marks: 80

Time- 3 Hrs

Answer any five Questions including Q No.1& 2
Figures in the right-hand margin indicates marks

1. Answer **All** questions. 2 x 10
 - a. Define pinch off voltage of an NMOS transistor.
 - b. Name the two lay out design rules of VLSI.
 - c. Define noise margins (NM_L and NM_H) of a CMOS inverter.
 - d. Implement XNOR gate using pass transistors.
 - e. Write the full forms of the following.
 1. ULSI
 2. EDA
 3. VHDL
 4. PLD
 - f. Define propagation delay of a CMOS inverter.
 - g. Number of transistors per chip ____ and minimum feature size ____ with the evolution in VLSI technology. (Increases, decreases)
 - h. Given $v_{GS} = 1.2V$, $V_{TN} = 0.6V$, $v_{DS} = 0.9V$. Calculate overdrive voltage (v_{OV}) and mention the region of operation of NMOS transistor.
 - i. What are the basic characteristics of an embedded system?
 - j. Find/Derive the condition for symmetric delay of a static CMOS inverter.
2. Answer **Any Six** Questions 6 x 5
 - a. Given $\mu_n C_{ox} = 160 \frac{\mu A}{V^2}$, $W = 0.36\mu m$, $L = 0.18\mu m$, $V_{TN} = 0.4V$. Consider NMOS transistor. For $v_{GS} = 0.6$, $v_{DS} = 1.0V$, indicate the region of operation of the transistor, and calculate the drain current i_D .
 - b. Realize a NOR2 gate using static CMOS and explain its working.
 - c. Design a clocked D latch using static CMOS.
 - d. What is FPGA? Explain its architecture with neat diagram.
 - e. Differentiate between SRAM and DRAM.

- f. Draw the stick diagram and lay out for static NAND2 gate.
- g. Find the worst-case Elmore parasitic delay of an n-input NAND gate.

3	Draw the steps for VLSI fabrication of an NMOS transistor.	10
4	Explain the construction and working of an enhancement type NMOS transistor and plot the graph between i_D and v_{DS} .	10
5	Explain the working of digital camera with the help of block diagram.	10
6	Describe VLSI design methodology, design flow and Y chart.	10
7	Implement full adder using static CMOS.	10